#2/IDS 6-1-99 GP 2812

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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject: Serial No. 09/285,986 04/05/99

S.S. Chen, Y.D. Sheu, C.H. Shen

A COST EFFECTIVE POLYIMIDE PROCESS TO SOLVE PASSIVATION EXTRUSION OR DAMAGE AND SOG DELAMINATES

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 4,733,289 to Tsurumaru, "Resin-Molded Semiconductor Device using Polyimide and Nitride Films for the Passivation Film", shows a resin-molded device using polyimide and nitride for passivation.

U.S. Patent 5,242,864 to Fassberg et al., "Polyimide Process for Protecting Integrated Circuits", shows a polyimide protection layer.

U.S. Patent 5,013,689 to Yamamoto et al., "Method of Forming a Passivation Film", shows a light sensitive polyimide layer used as a passivation layer.

U.S. Patent 5,091,289 to Cronin et al., "Process for Forming Multi-Level Coplanar Conductor/Insulator Films Employing Photosensitive Polyimide Polymer Compositions", shows a photosensitive polyimide composition.

U.S. Patent 5,187,119 to Cech et al., "Multichip Module and Integrated Circuit Substrates having Planarized Patterned Surfaces", shows a photosensitive polyimide and planarization process.

U.S. Patent 5,807,787 to Fu et al., "Method for Reduciing Surface Leakage Current on Semiconductor Integrated Circuits during Polyimide Passivation", discloses a polyimide passivation.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37661